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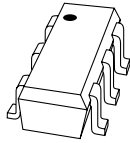
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Kind regards,

Team Nexperia



BC856S

65 V, 100 mA PNP/PNP general-purpose transistor

Rev. 02 — 19 February 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors

1.3 Applications

- General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	-65	V
I_C	collector current		-	-	-100	mA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V};$ $I_C = -2\text{ mA}$	110	-	-	

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		

sym018

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC856S	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BC856S	5F*

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

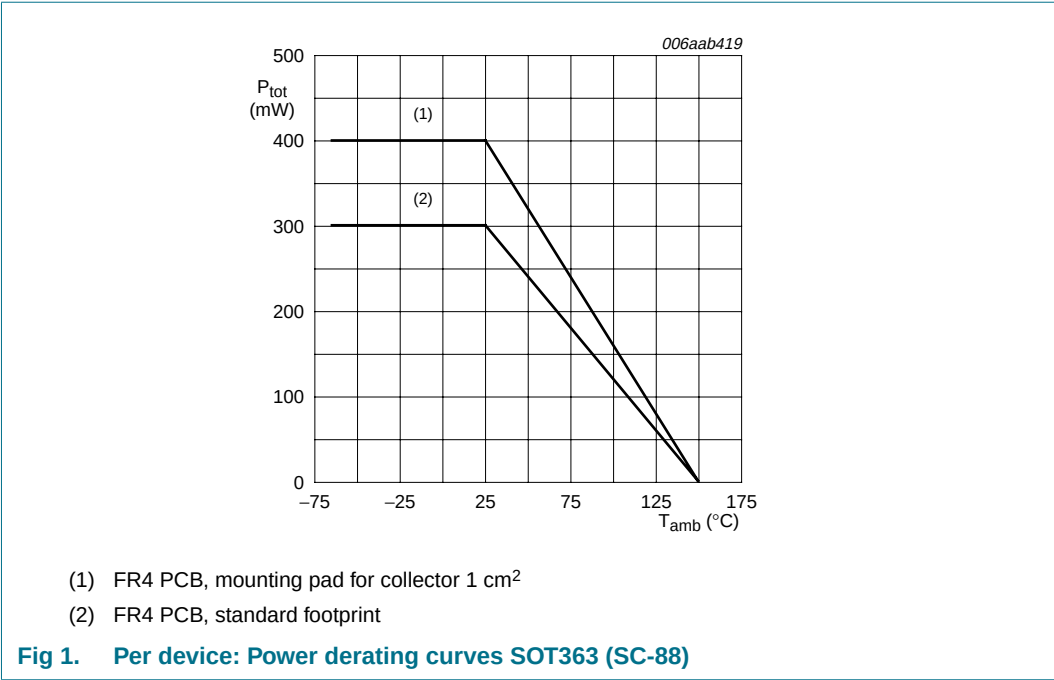
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transistor					
V _{CBO}	collector-base voltage	open emitter	-	−80	V
V _{CEO}	collector-emitter voltage	open base	-	−65	V
V _{EBO}	emitter-base voltage	open collector	-	−5	V
I _C	collector current		-	−100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	220	mW
			[2] -	250	mW
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	300	mW
			[2] -	400	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		−65	+150	°C
T _{stg}	storage temperature		−65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

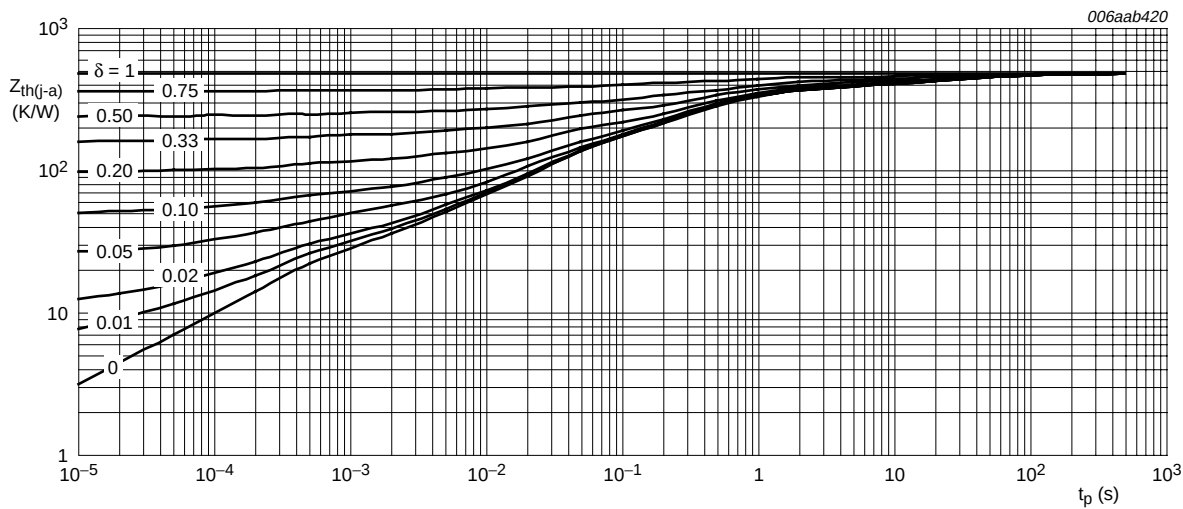
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



6. Thermal characteristics

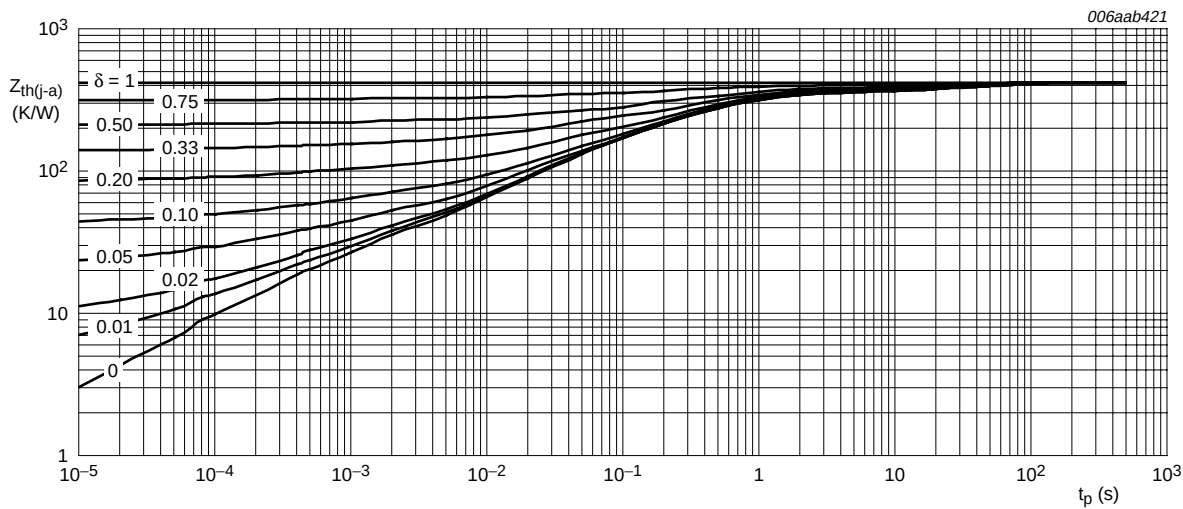
Table 6. Thermal characteristics						
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	568	K/W
			[2]	-	500	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	230	K/W
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	416	K/W
			[2]	-	313	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm^2

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

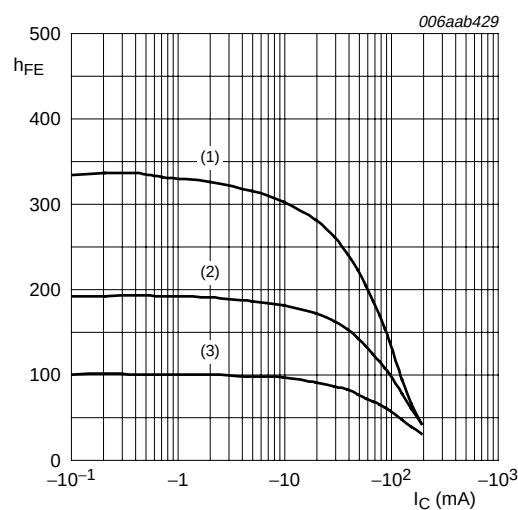
7. Characteristics

Table 7. Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

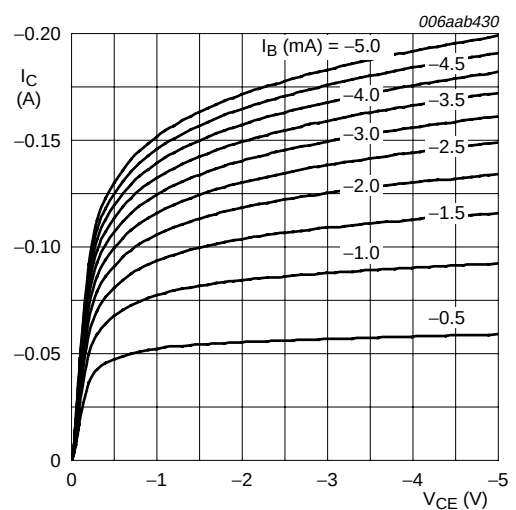
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
I_{CBO}	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0\text{ A}$	-	-	-15	nA
		$V_{CB} = -30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	-5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	-	-	-100	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}; I_C = -2\text{ mA}$	110	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	-	-	-100	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA}$ [1]	-	-	-300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	-	700	-	mV
V_{BE}	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	-600	-650	-750	mV
		$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}$	-	-	-820	mV
C_c	collector capacitance	$I_E = I_e = 0\text{ A}; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	-	-	2.5	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	-	-	MHz

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.



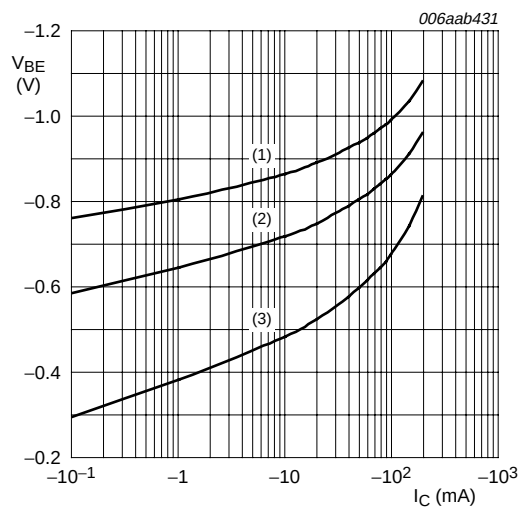
- $V_{CE} = -5\text{ V}$
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 4. Per transistor: DC current gain as a function of collector current; typical values



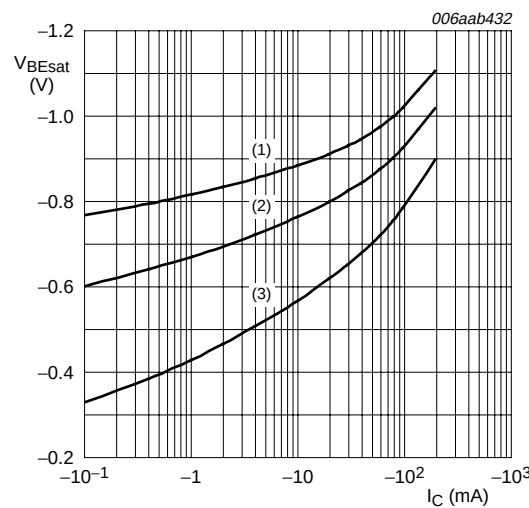
$T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 5. Per transistor: Collector current as a function of collector-emitter voltage; typical values



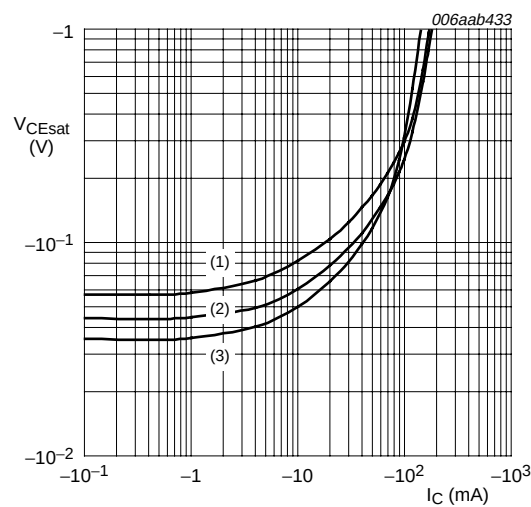
- $V_{CE} = -5\text{ V}$
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 6. Per transistor: Base-emitter voltage as a function of collector current; typical values



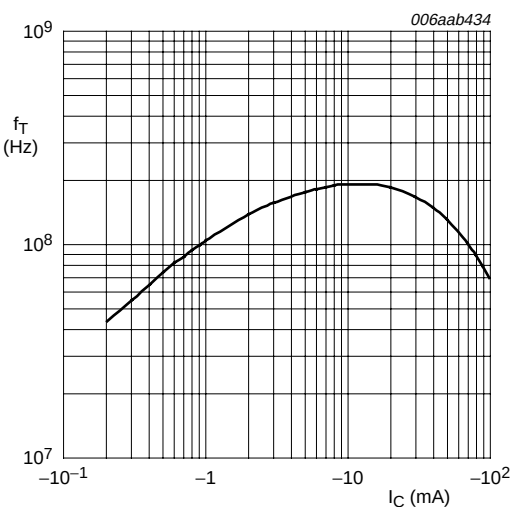
- $I_C/I_B = 20$
- (1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 7. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

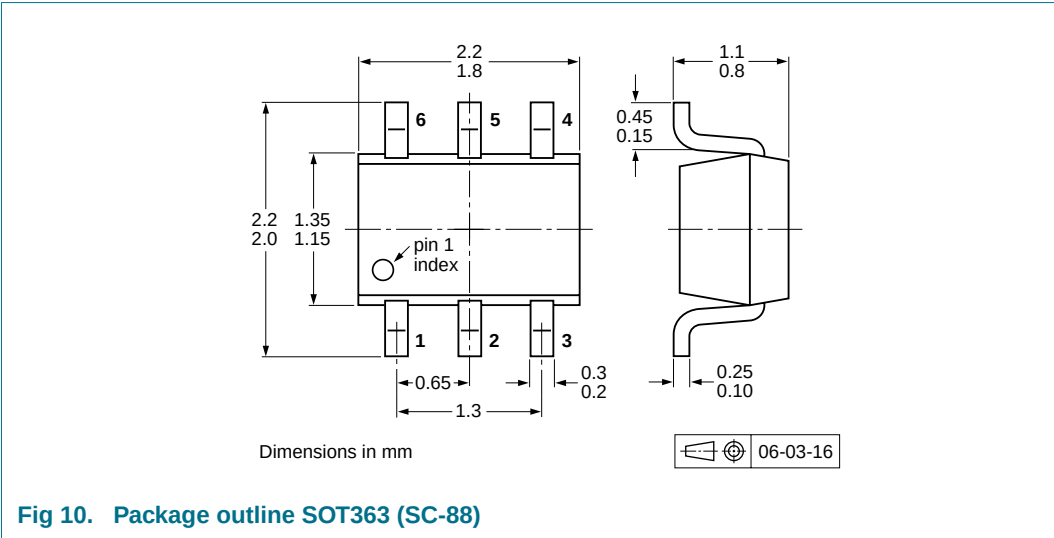
Fig 8. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values



$V_{CE} = -5\text{ V}$; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 9. Per transistor: Transition frequency as a function of collector current; typical values

8. Package outline



9. Packing information

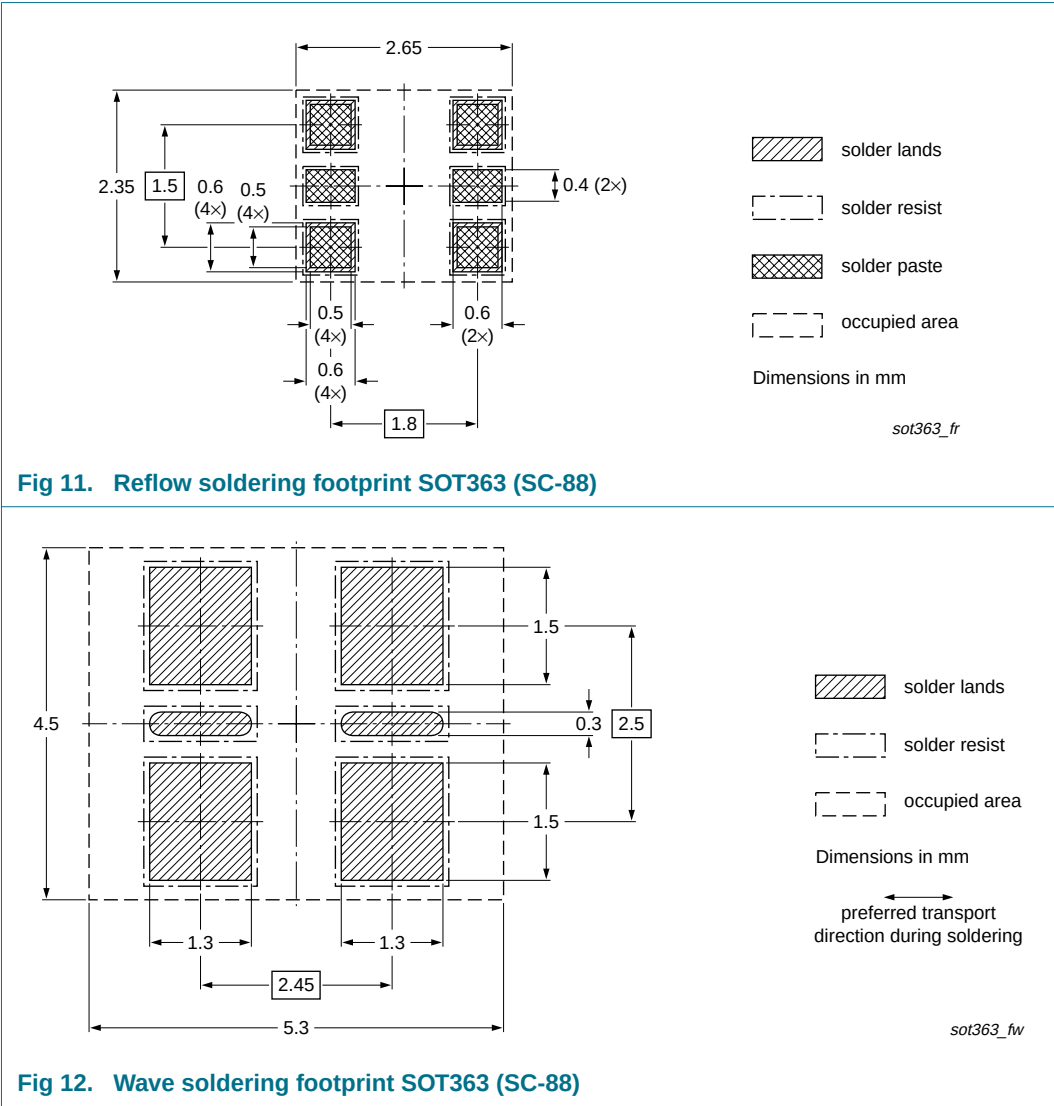
Table 8. Packing methods					
The indicated -xxx are the last three digits of the 12NC ordering code. ^[1]					
Type number	Package	Description	Packing quantity		
			3000	10000	
BC856S	SOT363	4 mm pitch, 8 mm tape and reel; T1	^[2] -115	-135	
		4 mm pitch, 8 mm tape and reel; T2	^[3] -125	-165	

[1] For further information and the availability of packing methods, see [Section 13](#).

[2] T1: normal taping

[3] T2: reverse taping

10. Soldering



11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC856S_2	20090219	Product data sheet	-	BC856S_1
Modifications:	- The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. - Legal texts have been adapted to the new company name where appropriate. Section 1.2 “Features”: adapted Section 4 “Marking”: updated Section 7 “Characteristics”: enhanced Section 9 “Packing information”: added Section 10 “Soldering”: added Section 12 “Legal information”: updated			
BC856S_1	19990824	Product specification	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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14. Contents

1 Product profile 1

1.1 General description. 1

1.2 Features 1

1.3 Applications 1

1.4 Quick reference data. 1

2 Pinning information. 1

3 Ordering information. 2

4 Marking 2

5 Limiting values. 2

6 Thermal characteristics. 3

7 Characteristics. 5

8 Package outline 8

9 Packing information. 8

10 Soldering 9

11 Revision history. 10

12 Legal information. 11

12.1 Data sheet status 11

12.2 Definitions 11

12.3 Disclaimers 11

12.4 Trademarks. 11

13 Contact information. 11

14 Contents 12



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